

HD74ALVC2G245

Dual Bus Transceivers with 3-state Output

REJ03D0176-0400Z (Previous ADE-205-641C (Z)) Rev.4.00 Dec.18.2003

Description

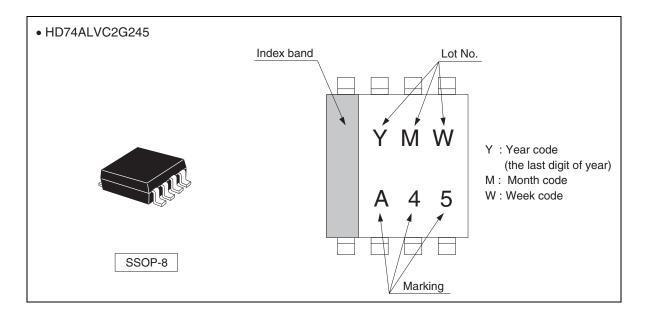
The HD74ALVC2G245 has two buffers with three state output in an 8 pin package. When DIR is high, data is transferred from the A inputs to the B outputs, and when DIR is low, data is transferred from the B inputs to the A outputs. The A and B buses are separated by making the enable input (\overline{OE}) high level. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range: 1.2 to 3.6 V
 Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 3.6 V (@V_{CC} = 0 V to 3.6 V) All outputs V_{O} (Max.) = 3.6 V (@V_{CC} = 0 V)
- $\begin{array}{ll} \bullet & \text{Output current} & \pm 2 \text{ mA } (@V_{CC} = 1.2 \text{ V}) \\ & \pm 4 \text{ mA } (@V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}) \\ & \pm 6 \text{ mA } (@V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}) \\ & \pm 18 \text{ mA } (@V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}) \\ & \pm 24 \text{ mA } (@V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}) \end{array}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74ALVC2G245USE	SSOP-8 pin	TTP-8DBV	US	E (3,000 pcs/reel)

Outline and Article Indication



Function Table

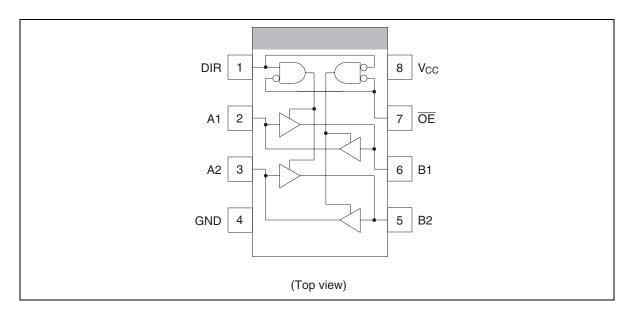
Inputs

ŌĒ	DIR	Operation
L	L	B data to A bus
L	Н	A data to B bus
Н	X	Isolation

H: High level L: Low level

X: Immaterial

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V_{CC}	-0.5 to 4.6	V	
Input voltage range *1	Vı	-0.5 to 4.6	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} +0.5	V	Output : H or L or Z
		-0.5 to 4.6	_	V _{CC} : OFF
Input clamp current	I _{IK}	-50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	lo	±50	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

HD74ALVC2G245

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	1.2	3.6	V	
Input voltage range	Vı	0	3.6	V	
Output voltage range	Vo	0	V _{CC}	V	
Output current	I _{OH}		-2	mA	V _{CC} = 1.2 V
		_	-4		V _{CC} = 1.4 V
		_	-6		V _{CC} = 1.65 V
		_	-18		$V_{CC} = 2.3 \text{ V}$
		_	-24		V _{CC} = 3.0 V
	I _{OL}	_	2		V _{CC} = 1.2 V
		_	4		V _{CC} = 1.4 V
		_	6		V _{CC} = 1.65 V
		_	18		$V_{CC} = 2.3 \text{ V}$
		_	24		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fall rate	Δt / Δν	0	20	ns / V	V _{CC} = 1.2 to 2.7 V
		0	10		V _{CC} = 3.3±0.3 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	$V_{CC}(V)^*$	Min	Тур	Max	Unit	Test conditions
Input voltage	V _{IH}	1.2	V _{CC} ×0.75	_	_	V	
		1.4 to 1.6	V _{CC} ×0.7	_	_	=	
		1.65 to 1.95	V _{CC} ×0.7	_	_	-	
		2.3 to 2.7	1.7	_	_	=	
		3.0 to 3.6	2.0	_	_	=	
	V _{IL}	1.2	_	_	V _{CC} ×0.25	-	
		1.4 to 1.6	_	_	V _{CC} ×0.3	-	
		1.65 to 1.95	_	_	V _{CC} ×0.3	-	
		2.3 to 2.7	_	_	0.7	-	
		3.0 to 3.6	_	_	0.8	=	
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	_	_	V	$I_{OH} = -100 \mu A$
		1.2	0.9	_	_	=	$I_{OH} = -2 \text{ mA}$
		1.4	1.1	_	_	=	$I_{OH} = -4 \text{ mA}$
		1.65	1.2	_	_	=	$I_{OH} = -6 \text{ mA}$
		2.3	1.7	_	_	-	$I_{OH} = -18 \text{ mA}$
		3.0	2.2	_	_	=	$I_{OH} = -24 \text{ mA}$
	V _{OL}	Min to Max	_	_	0.2	-	$I_{OL} = 100 \mu\text{A}$
		1.2	_	_	0.3	-	I _{OL} = 2 mA
		1.4	_	_	0.3	=	I _{OL} = 4 mA
		1.65	_	_	0.3	=	I _{OL} = 6 mA
		2.3	_	_	0.55	-	I _{OL} = 18 mA
		3.0	_	_	0.55	=	I _{OL} = 24 mA
Input current	I _{IN}	3.6	_	_	±5	μΑ	$V_{IN} = 3.6 \text{ V or GND}$
Off state output current	l _{OZ}	3.6	_		±5	μΑ	$V_O = V_{CC}$ or GND
Quiescent supply current	I _{CC}	3.6	_	_	10	μΑ	$V_{IN} = V_{CC}$ or GND, $I_O = 0$
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V _{IN} or V _O = 0 to 3.6 V
Input capacitance	C _{IN}	3.3	_	4.5		pF	$V_{IN} = V_{CC}$ or GND
Output capacitance	Co	3.3	_	6.5	_	pF	$V_0 = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

 $V_{CC} = 1.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}		7.0	_	ns	C _L = 15 pF	A or B	B or A
Enable time	t _{ZH} t _{ZL}	_	8.5	_	ns	C _L = 15 pF	ŌĒ	A or B
Disable time	t _{HZ} t _{LZ}	_	7.0	_	ns	C _L = 15 pF	ŌĒ	A or B

 $V_{CC} = 1.5 \pm 0.1 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	2.0	_	8.0	ns	$C_L = 15 pF$	A or B	B or A
Enable time	t _{ZH}	2.0	_	11.0	ns	C _L = 15 pF	ŌĒ	A or B
Disable time	t _{HZ} t _{LZ}	2.0	_	10.0	ns	$C_L = 15 pF$	ŌĒ	A or B

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.5	_	6.0	ns	$C_L = 30 pF$	A or B	B or A
Enable time	t _{ZH} t _{ZL}	1.5	_	8.0	ns	C _L = 30 pF	ŌĒ	A or B
Disable time	t _{HZ} t _{LZ}	1.5	_	7.5	ns	C _L = 30 pF	ŌĒ	A or B

Switching Characteristics (cont)

 $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	4.0	ns	$C_L = 30 pF$	A or B	B or A
Enable time	t _{ZH} t _{ZL}	1.0	_	5.0	ns	$C_L = 30 pF$	ŌĒ	A or B
Disable time	t _{HZ} t _{LZ}	1.0	_	4.5	ns	$C_L = 30 pF$	ŌĒ	A or B

 $V_{CC} = 3.3 \pm 0.3 \text{ V}$

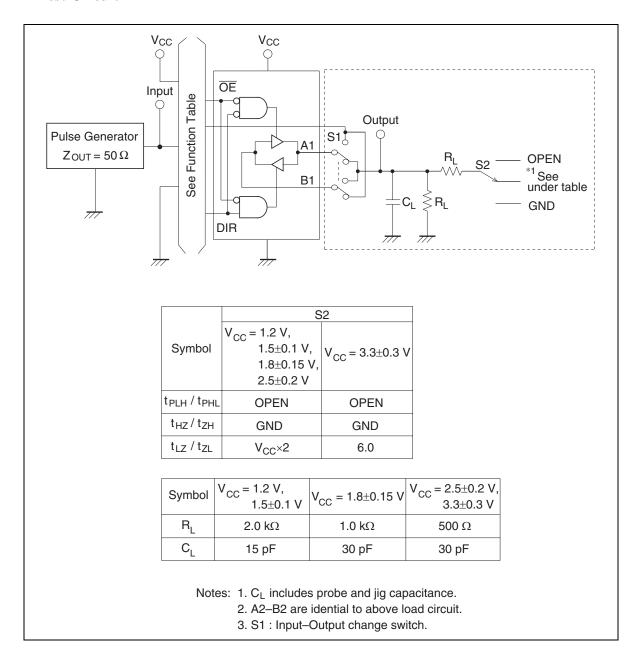
Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	3.0	ns	$C_L = 30 pF$	A or B	B or A
Enable time	t _{ZH} t _{ZL}	1.0	_	4.0	ns	C _L = 30 pF	ŌĒ	A or B
Disable time	t_{HZ}	1.0	_	4.0	ns	$C_L = 30 pF$	ŌĒ	A or B

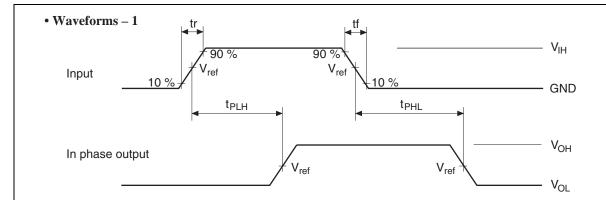
Operating Characteristics

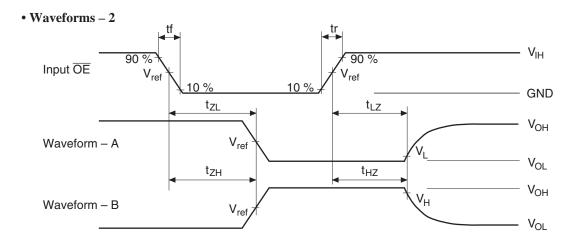
 $(Ta = 25^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation capacitance	C _{PD}	1.5	_	13.0		pF	f = 10 MHz
		1.8	_	13.0		_	
		2.5	_	14.0		_	
		3.3	_	17.0		_	

Test Circuit





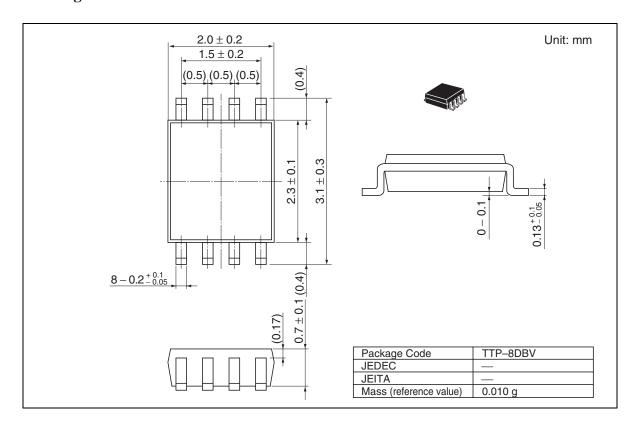


Symbol	V _{CC} = 1.2 V, 1.5±0.1 V	V _{CC} = 1.8±0.15 V	V _{CC} = 2.5±0.2 V	$V_{CC} = 3.3 \pm 0.3 \text{ V}$
t _r /t _f	2.0 ns	2.0 ns	2.5 ns	2.5 ns
V _{IH}	V _{CC}	V _{CC}	V _{CC}	2.7 V
V _{ref}	50%	50%	50%	1.5 V
V _H / V _L	$V_{H} = V_{OH}-0.1 V$ $V_{L} = V_{OL}+0.1 V$		$V_H = V_{OH}$ -0.15 V $V_L = V_{OL}$ +0.15 V	$V_H = V_{OH} - 0.3 V$ $V_L = V_{OL} + 0.3 V$

Notes: 1. Input waveform : PRR \leq 10 MHz, Zo = 50 Ω , duty cycle 50%.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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